



PATENT  
Customer No. 22,852  
Attorney Docket No. 02887.0141-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Yukihito OOWAKI et al.

Application No.: 09/879,208

Filed: June 13, 2001

For: MIS TRANSISTOR AND METHOD  
FOR PRODUCING THE SAME

Group Art Unit: 2814

Examiner: S. Rao

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

**AMENDMENT**

In reply to the Office Action of January 23, 2003, the period for reply to which extends through April 23, 2003, please amend this application as follows:

**IN THE CLAIMS:**

Please amend claims 14, 18, 22, and 27, as follows:

14. (Twice Amended) A method for producing a MIS transistor comprising a semiconductor substrate, source/drain regions formed on the semiconductor substrate, and a gate electrode provided above a channel region between the source/drain regions, said method comprising:

selectively forming a first film on said semiconductor substrate;

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